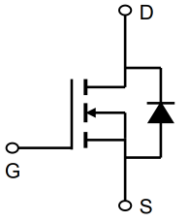
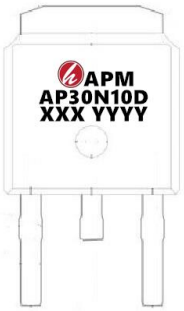
AP30N10D

100V N-Channel Enhancement Mode MOSFET

Description

The AP30N10D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.





General Features

V_{DS} = 100V I_D = 30A

$R_{DS(ON)}$ < 47mΩ @ V_{GS}=10V

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP30N10D	TO-252-3L	AP30N10D XXX YYYY	2500

Absolute Maximum Ratings T_C=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	30	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	13.5	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	4.2	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	3.4	A
I_{DM}	Pulsed Drain Current[2]	45	A
EAS	Single Pulse Avalanche Energy[3]	36.5	mJ
I_{AS}	Avalanche Current	27	A
P_D@T_C=25℃	Total Power Dissipation[4]	52.1	W
P_D@T_A=25℃	Total Power Dissipation[4]	2	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	2.4	℃/W

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Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.098	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	38	47	mΩ
		V_{GS}=4.5V , I_D=15A	---	40	50	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.3	---	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.52	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25℃	---	---	10	uA
		V_{DS}=80V , V_{GS}=0V , T_J=55℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=20A	---	28.7	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.6	3.2	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=80V , V_{GS}=10V , I_D=20A	---	60	84	nC
Q_{gs}	Gate-Source Charge		---	9.7	14	
Q_{gd}	Gate-Drain Charge		---	11.8	16.5	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=50V , V_{GS}=10V , R_G=3.3Ω I_D=20A	---	10.4	21	ns
T_r	Rise Time		---	46	83	
$T_{d(off)}$	Turn-Off Delay Time		---	54	108	
T_f	Fall Time		---	10	20	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	3848	5387	pF
C_{oss}	Output Capacitance		---	137	192	
C_{rss}	Reverse Transfer Capacitance		---	82	115	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	22	A
I_{SM}	Pulsed Source Current[2,5]		---	---	45	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=20A , dI/dt=100A/μs , T_J=25℃	---	30	---	nS
Q_{rr}	Reverse Recovery Charge		---	37	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=27A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

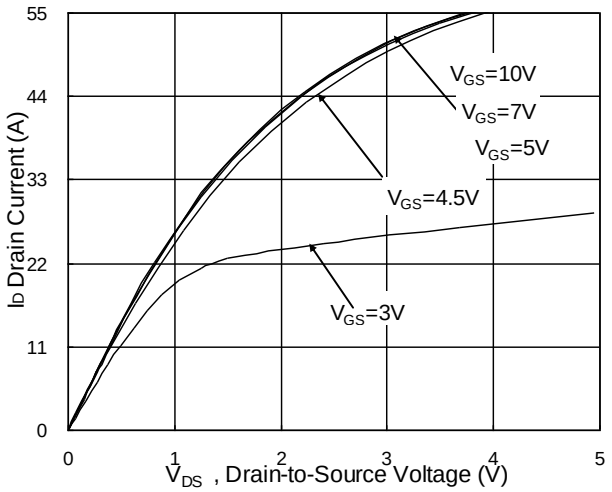

Fig.1 Typical Output Characteristics

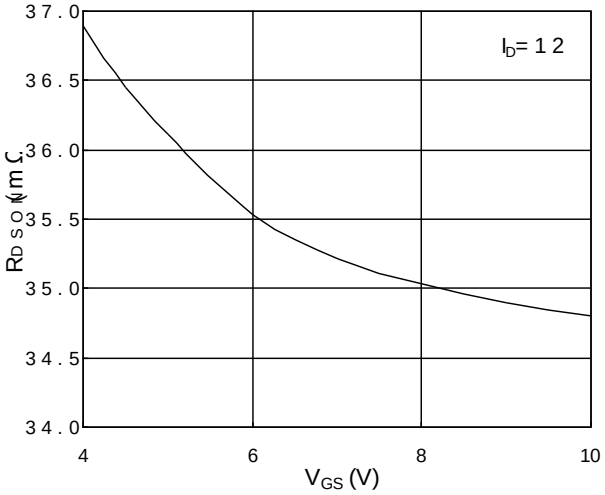

Fig.2 On-Resistance vs. Gate-Source

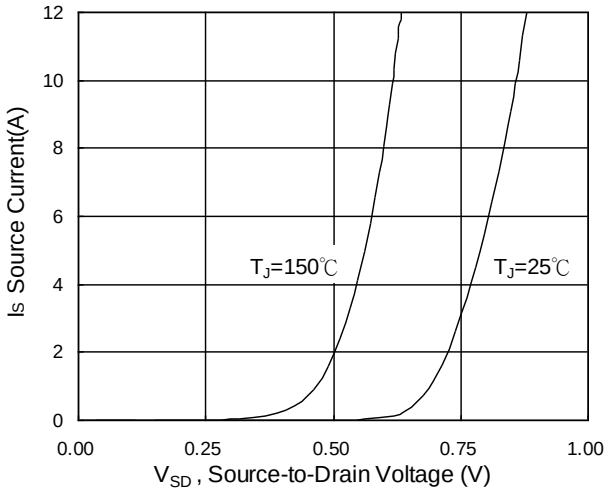

Fig.3 Forward Characteristics Of Reverse

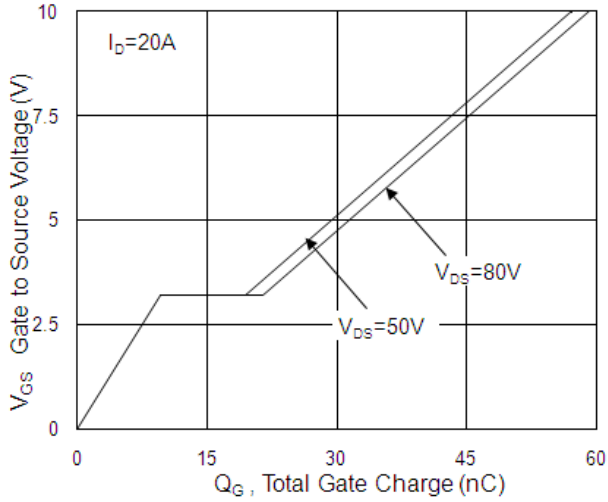

Fig.4 Gate-Charge Characteristics

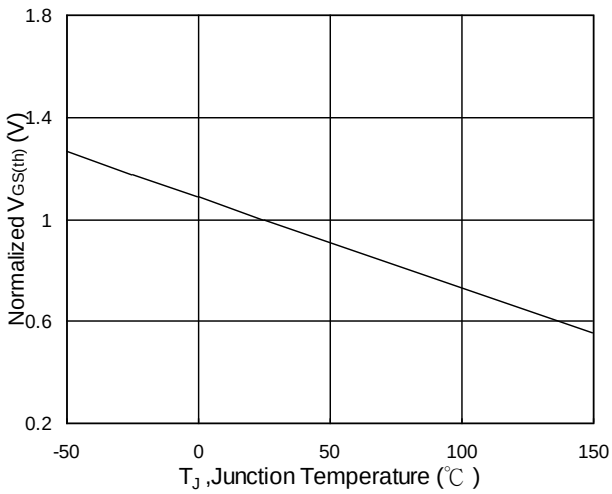

Fig.5 Normalized $V_{GS(th)}$ vs. T_J

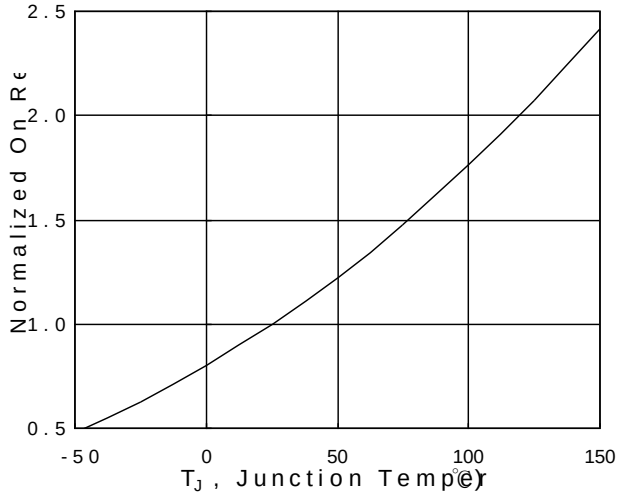

Fig.6 Normalized R_{DSON} vs. T_J

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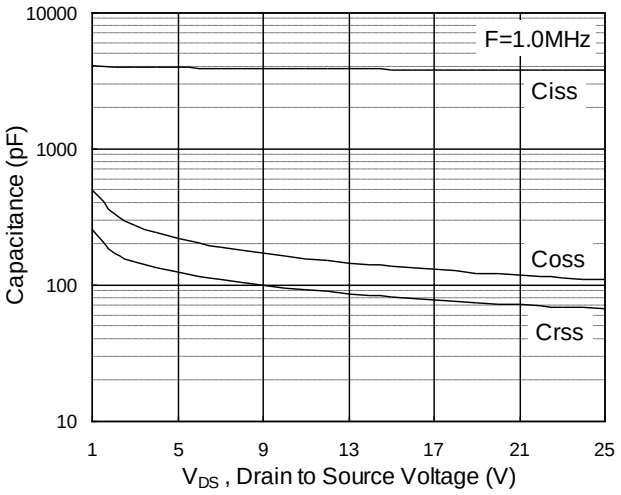

Fig.7 Capacitance

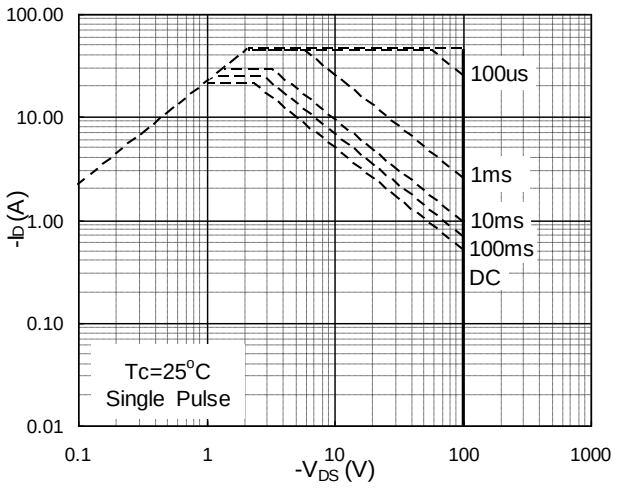

Fig.8 Safe Operating Area

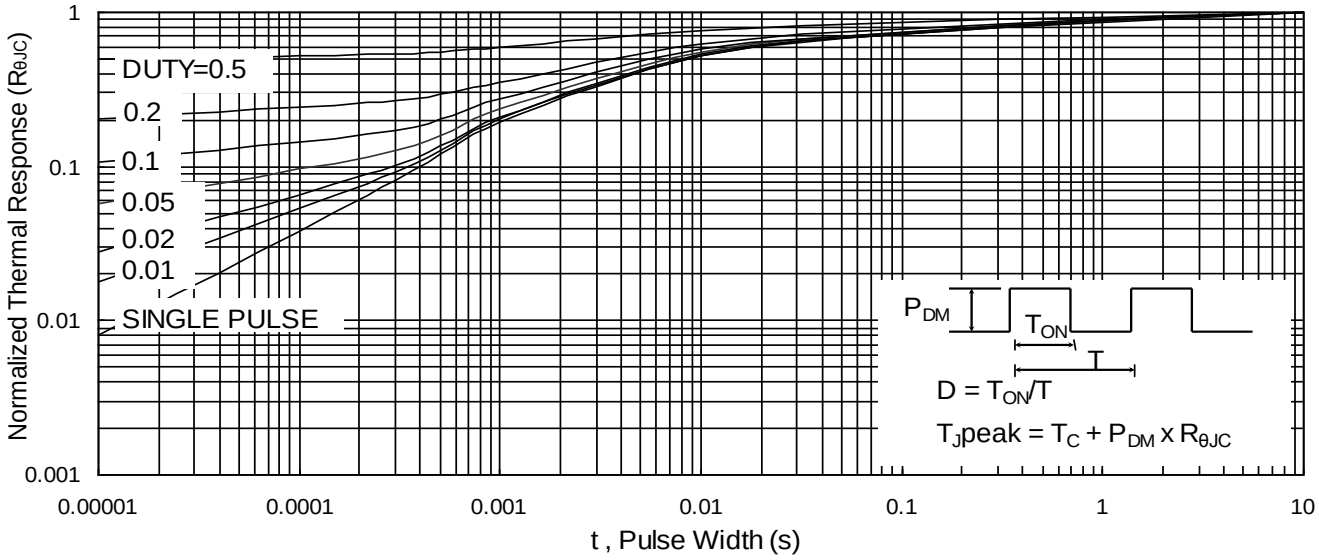

Fig.9 Normalized Maximum Transient Thermal Impedance

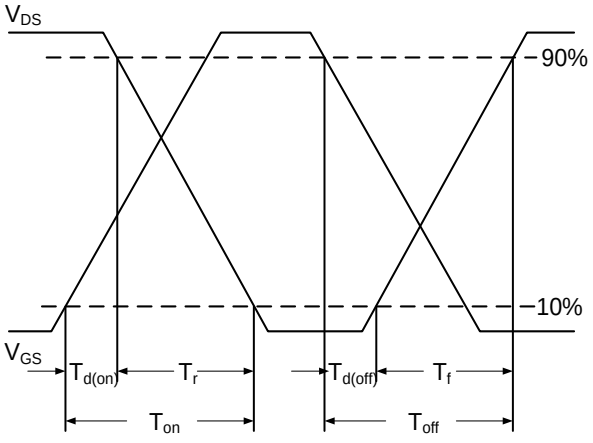

Fig.10 Switching Time Waveform

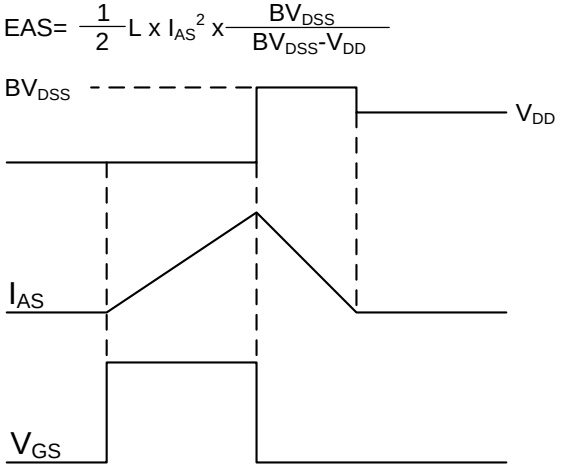

Fig.11 Unclamped Inductive Switching Waveform

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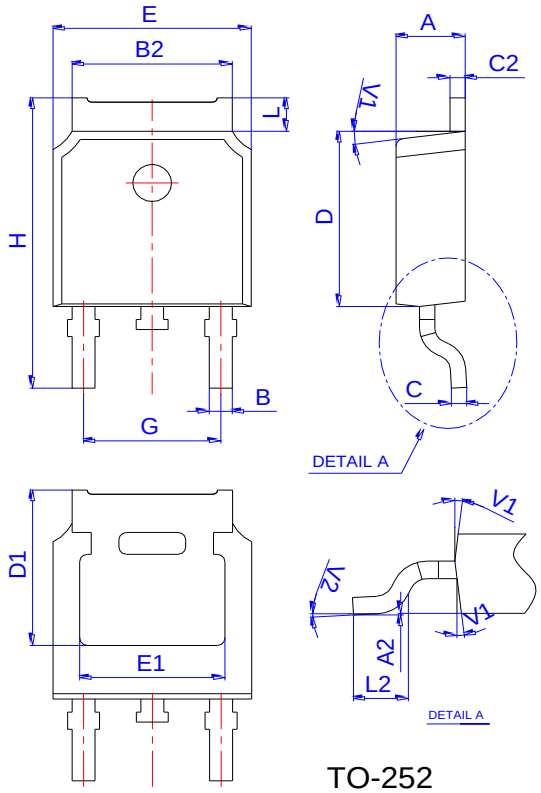
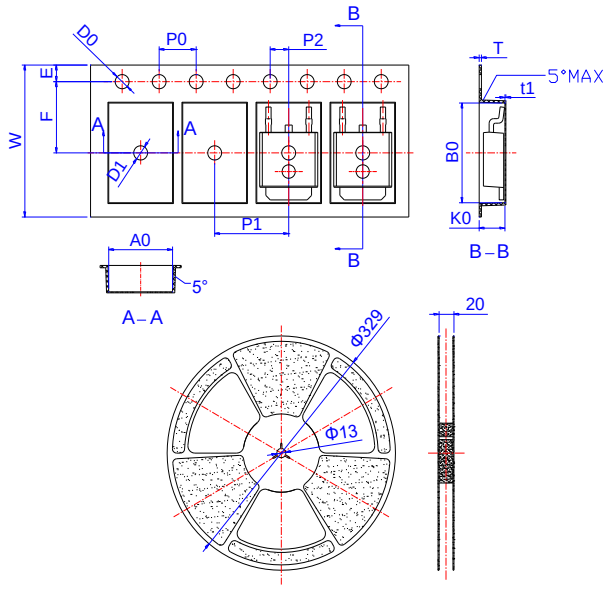
Package Mechanical Data



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Spectification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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